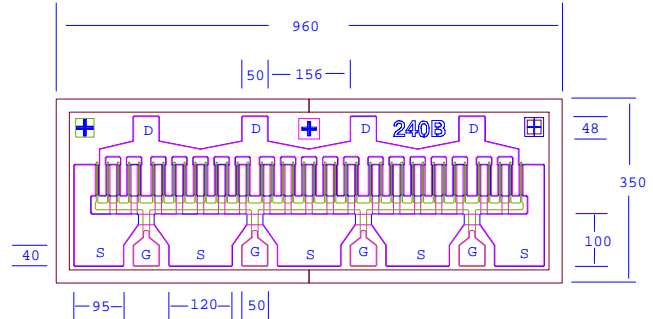


**PRELIMINARY DATA SHEET**
**Low Distortion GaAs Power FET**

- +31.0dBm TYPICAL OUTPUT POWER
- 8.5dB TYPICAL POWER GAIN AT 12GHz
- HIGH BV<sub>gd</sub> FOR 10V BIAS
- 0.3 X 2400 MICRON RECESSED “MUSHROOM” GATE
- Si<sub>3</sub>N<sub>4</sub> PASSIVATION
- ADVANCED EPITAXIAL DOPING PROFILE PROVIDES HIGH POWER EFFICIENCY, LINEARITY AND RELIABILITY
- Id<sub>ss</sub> SORTED IN 40mA PER BIN RANGE



Chip Thickness: 75 ± 13 microns  
All Dimensions In Microns

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)**

SYMBOLS	PARAMETERS/TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>P<sub>1dB</sub></b>	Output Power at 1dB Compression V <sub>ds</sub> =10V, I <sub>ds</sub> =50% I <sub>ds</sub>	29.0	31.0 31.0		dBm
<b>G<sub>1dB</sub></b>	Gain at 1dB Compression V <sub>ds</sub> =10V, I <sub>ds</sub> =50% I <sub>ds</sub>	7.0	8.5 6.0		dB
<b>PAE</b>	Power Added Efficiency at 1dB compression V <sub>ds</sub> =10V, I <sub>ds</sub> =50% I <sub>ds</sub>		33		%
<b>I<sub>ds</sub></b>	Saturated Drain Current V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	320	520	720	mA
<b>G<sub>m</sub></b>	Transconductance V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	200	280		mS
<b>V<sub>p</sub></b>	Pinch-off Voltage V <sub>ds</sub> =3V, I <sub>ds</sub> =6mA		-2.5	-4.0	V
<b>BV<sub>gd</sub></b>	Drain Breakdown Voltage I <sub>gd</sub> =2.4mA	-15	-20		V
<b>BV<sub>gs</sub></b>	Source Breakdown Voltage I <sub>gs</sub> =2.4mA	-10	-17		V
<b>R<sub>th</sub></b>	Thermal Resistance (Au-Sn Eutectic Attach)		20		°C/W

**MAXIMUM RATINGS AT 25°C**

SYMBOLS	PARAMETERS	ABSOLUTE <sup>1</sup>	CONTINUOUS <sup>2</sup>
<b>V<sub>ds</sub></b>	Drain-Source Voltage	14V	10V
<b>V<sub>gs</sub></b>	Gate-Source Voltage	-8V	-4.5V
<b>I<sub>ds</sub></b>	Drain Current	I <sub>ds</sub>	570mA
<b>I<sub>gsf</sub></b>	Forward Gate Current	60mA	10mA
<b>P<sub>in</sub></b>	Input Power	29dBm	@ 3dB Compression
<b>T<sub>ch</sub></b>	Channel Temperature	175°C	150°C
<b>T<sub>stg</sub></b>	Storage Temperature	-65/175°C	-65/150°C
<b>P<sub>t</sub></b>	Total Power Dissipation	6.8 W	5.7 W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

**Excelics Semiconductor, Inc., 2908 Scott Blvd., Santa Clara, CA 95054**  
**Phone: (408) 970-8664 Fax: (408) 970-8998 Web Site: www.excelics.com**

# EFC240B

## PRELIMINARY DATA SHEET

### Low Distortion GaAs Power FET

#### S-PARAMETERS

10V, 1/2 Idss

Freq	S11	S11	S21	S21	S12	S12	S22	S22
GHz	Mag	Ang	Mag	Ang	Mag	Ang	Mag	Ang
1.000	0.944	-86.7	7.064	130.8	0.041	41.9	0.296	-132.9
2.000	0.915	-125.9	4.551	104.6	0.052	22.7	0.374	-146.8
3.000	0.907	-144.8	3.217	89.3	0.055	13.2	0.409	-152.2
4.000	0.907	-155.6	2.450	78.1	0.054	6.7	0.433	-154.1
5.000	0.912	-161.6	1.929	69.0	0.052	2.7	0.460	-157.6
6.000	0.911	-166.1	1.596	60.9	0.050	0.1	0.487	-158.3
7.000	0.920	-169.0	1.362	54.1	0.049	-2.2	0.512	-159.2
8.000	0.915	-171.1	1.181	47.7	0.047	-3.4	0.549	-161.0
9.000	0.919	-173.3	1.040	41.7	0.045	-4.5	0.586	-161.9
10.000	0.922	-176.1	0.922	35.7	0.041	-5.2	0.620	-162.0
11.000	0.925	-179.2	0.826	30.0	0.041	-6.2	0.647	-162.2
12.000	0.932	178.8	0.747	24.7	0.039	-7.5	0.673	-163.2
13.000	0.933	177.0	0.681	19.1	0.037	-7.5	0.690	-165.6
14.000	0.939	175.4	0.622	13.8	0.035	-7.7	0.716	-168.5
15.000	0.941	172.9	0.569	8.5	0.035	-7.0	0.739	-170.1
16.000	0.945	170.6	0.522	3.0	0.035	-6.4	0.752	-172.8
17.000	0.946	169.7	0.483	-2.1	0.035	-7.5	0.764	-177.3
18.000	0.952	170.3	0.452	-7.0	0.034	-6.2	0.776	176.4
19.000	0.955	170.4	0.421	-12.7	0.034	-6.5	0.791	169.8
20.000	0.955	168.7	0.387	-18.0	0.035	-3.8	0.813	164.9
21.000	0.954	160.5	0.359	-23.1	0.034	-5.3	0.835	168.3
22.000	0.948	158.1	0.327	-26.7	0.035	-2.1	0.847	166.2
23.000	0.958	157.0	0.303	-30.7	0.035	0.6	0.870	163.7
24.000	0.956	156.1	0.275	-33.9	0.036	2.9	0.876	162.1
25.000	0.961	155.3	0.251	-36.4	0.038	7.7	0.887	160.5
26.000	0.954	153.5	0.232	-39.0	0.036	10.4	0.897	160.1

Note: The data included 0.7 mils diameter Au bonding wires:  
4 gate wires, 15 mils each; 4 drain wires, 20 mils each; 10 source wires, 7 mils each.